Switch-mode Schottky Power Rectifier

DPAK Power Surface Mount Package

The NRVBD1035CTL employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency switching power supplies, free wheeling diode and polarity protection diodes.

Features

- Highly Stable Oxide Passivated Junction
- Guardring for Stress Protection
- Matched Dual Die Construction –
 May be Paralleled for High Current Output
- High dv/dt Capability
- Short Heat Sink Tap Manufactured Not Sheared
- Very Low Forward Voltage Drop
- Epoxy Meets UL 94 V-0 @ 0.125 in
- This is a Pb-Free Device

Mechanical Characteristics:

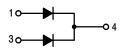
- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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SCHOTTKY BARRIER RECTIFIER 10 AMPERES 35 VOLTS





MARKING DIAGRAM



A = Assembly Location Y = Year

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	35	V
Average Rectified Forward Current (At Rated V_R , $T_C = 115^{\circ}C$)	Per Leg Per Package	Io	5.0 10	А
Peak Repetitive Forward Current (At Rated V _R , Square Wave, 20 kHz, T _C = 115°C)	Per Leg	I _{FRM}	10	Α
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, sir	Per Package ngle phase, 60 Hz)	I _{FSM}	50	А
Storage / Operating Case Temperature		T _{stg,} T _c	-55 to +150	°C
Operating Junction Temperature (Note 1)		TJ	-55 to +150	°C
Voltage Rate of Change (Rated V _R , T _J = 25°C)		dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	Per Leg	$R_{ heta JC}$	3.0	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	Per Leg	$R_{ heta JA}$	137	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 3) (See Figure 2) $I_F = 5 \text{ Amps, } T_J = 25^{\circ}\text{C}$ $I_F = 5 \text{ Amps, } T_J = 100^{\circ}\text{C}$ $I_F = 10 \text{ Amps, } T_J = 25^{\circ}\text{C}$ $I_F = 10 \text{ Amps, } T_J = 100^{\circ}\text{C}$	Per Leg	V _F	0.47 0.41 0.56 0.55	V
Maximum Instantaneous Reverse Current (Note 3) (See Figure 4) $ (V_R = 35 \text{ V}, T_J = 25^{\circ}\text{C}) $ $ (V_R = 35 \text{ V}, T_J = 100^{\circ}\text{C}) $ $ (V_R = 17.5 \text{ V}, T_J = 25^{\circ}\text{C}) $ $ (V_R = 17.5 \text{ V}, T_J = 100^{\circ}\text{C}) $	Per Leg	I _R	2.0 30 0.20 5.0	mA

^{2.} Rating applies when using minimum pad size, FR4 PC Board

ORDERING INFORMATION

Device	Package	Shipping [†]
NRVBD1035CTLT4G	DPAK (Pb-Free)	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

^{3.} Pulse Test: Pulse Width ≤ 250 µs, Duty Cycle ≤ 2.0%

TYPICAL CHARACTERISTICS

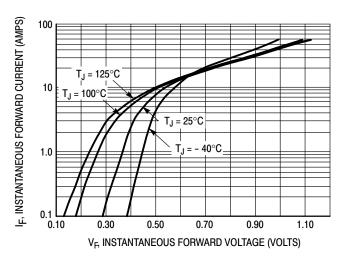
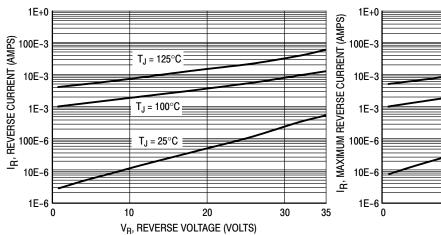


Figure 1. Typical Forward Voltage Per Leg

Figure 2. Maximum Forward Voltage Per Leg



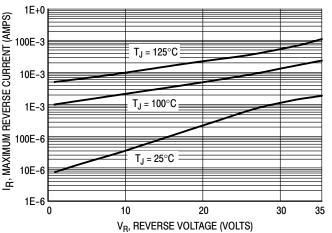


Figure 3. Typical Reverse Current Per Leg

Figure 4. Maximum Reverse Current Per Leg

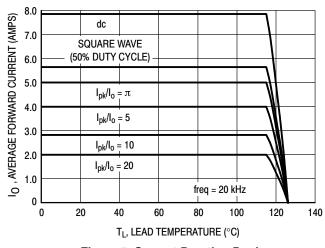


Figure 5. Current Derating Per Leg

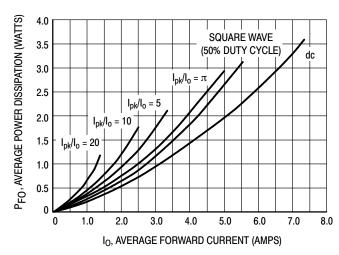


Figure 6. Forward Power Dissipation Per Leg

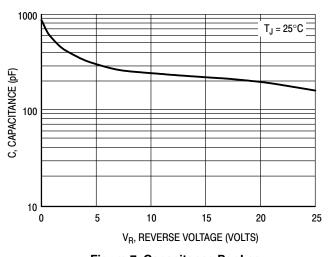


Figure 7. Capacitance Per Leg

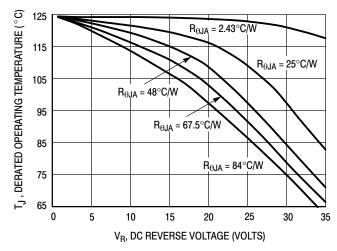


Figure 8. Typical Operating Temperature
Derating Per Leg *

r(t) = thermal impedance under given conditions,

Pf = forward power dissipation, and

Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

^{*} Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t) (Pf + Pr) \text{ where}$

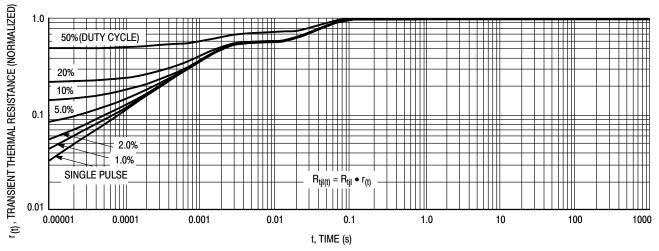


Figure 9. Thermal Response Junction to Case (Per Leg)

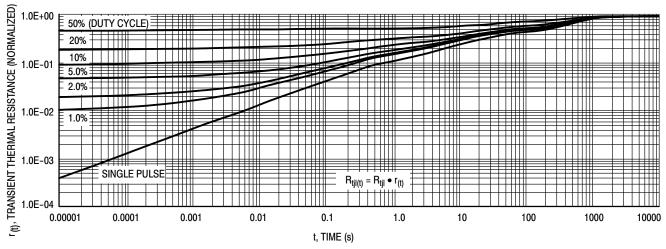
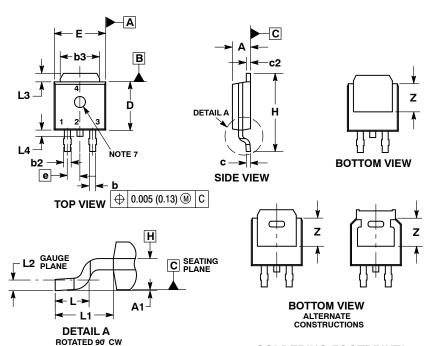


Figure 10. Thermal Response Junction to Ambient (Per Leg)

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)

CASE 369C **ISSUE F**

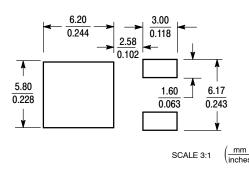


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
 2. CONTROLLING DIMENSION: INCHES.
 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-MENSIONS b3, L3 and Z.
- MEISTONS D. S. BILLS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020	BSC	0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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